



MJD47

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

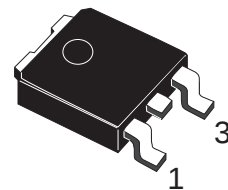
- STMicroelectronics PREFERRED SALESTYPE
- HIGH VOLTAGE CAPABILITY
- SURFACE-MOUNTING TO-252 (DPAK) POWER PACKAGE IN TAPE & REEL (SUFFIX "T4")
- ELECTRICALLY SIMILAR TO TIP47

APPLICATIONS

- SWITCH MODE POWER SUPPLIES
- AUDIO AMPLIFIERS
- GENERAL PURPOSE SWITCHING AND AMPLIFIER

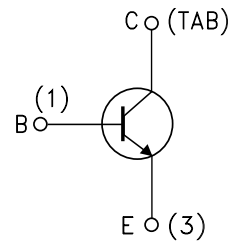
DESCRIPTION

The MJD47 is manufactured using Medium Voltage Epitaxial Planar technology, resulting in a rugged high performance cost-effective transistor.



**DPAK
TO-252**
(Suffix "T4")

INTERNAL SCHEMATIC DIAGRAM



SC07670

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	350	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	250	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	5	V
I_C	Collector Current	1	A
I_{CM}	Collector Peak Current ($t_p < 5$ ms)	2	A
I_B	Base Current	0.6	A
I_{BM}	Base Peak Current ($t_p < 5$ ms)	1.2	A
P_{tot}	Total Dissipation at $T_c = 25$ °C	15	W
T_{stg}	Storage Temperature	-65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

MJD47

THERMAL DATA

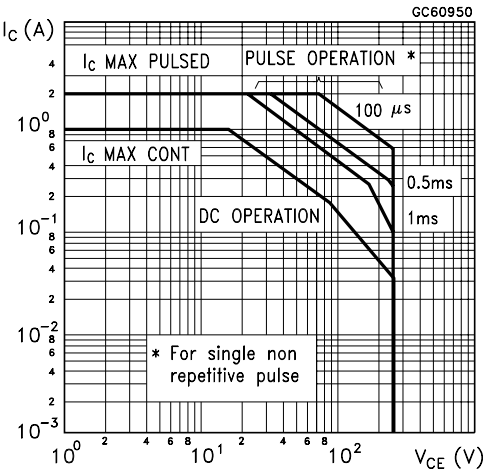
Rthj-case	Thermal Resistance Junction-case	Max	8.33	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Max	100	°C/W

ELECTRICAL CHARACTERISTICS (Tcase = 25 °C unless otherwise specified)

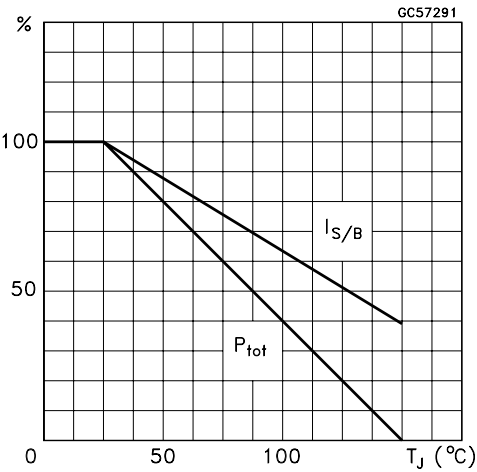
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
ICES	Collector Cut-off Current (VBE = 0)	VCE = 350 V			0.1	mA
ICEO	Collector Cut-off Current (IB = 0)	VCE = 150 V			0.1	mA
IEBO	Emitter Cut-off Current (IC = 0)	VEB = 5 V			1	mA
VCEO(sus)*	Collector-Emitter Sustaining Voltage (IB = 0)	IC = 30 mA	250			V
VCE(sat)*	Collector-Emitter Saturation Voltage	IC = 1 A IB = 0.2 A			1	V
VBE(on)*	Base-Emitter On Voltage	IC = 1 A VCE = 10 V			1.5	V
hFE*	DC Current Gain	IC = 0.3 A VCE = 10 V IC = 1 A VCE = 10 V	30 10		150	
fT	Transition Frequency	IC = 0.2 A VCE = 10 V f = 2MHz	10			MHz
hfe	Small Signal Current Gain	IC = 0.2 A VCE = 10 V f = 1KHz	25			

* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

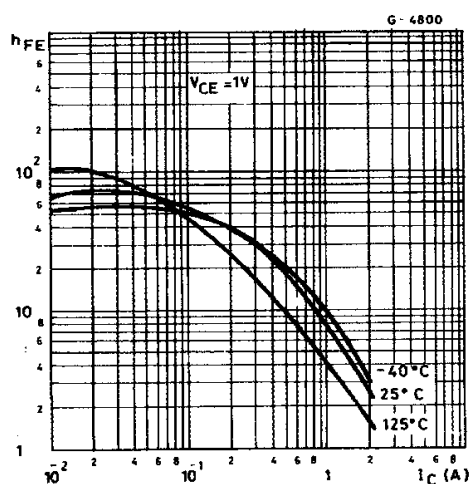
Safe Operating Area



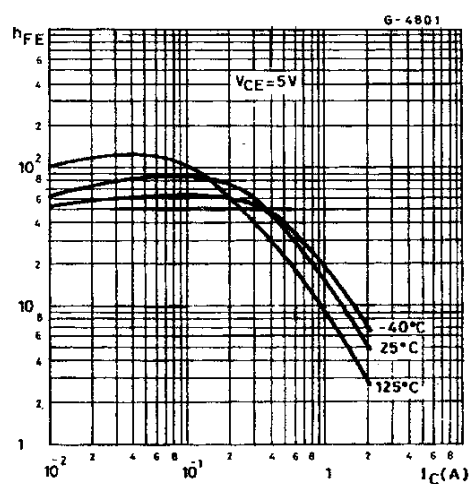
Derating Curves



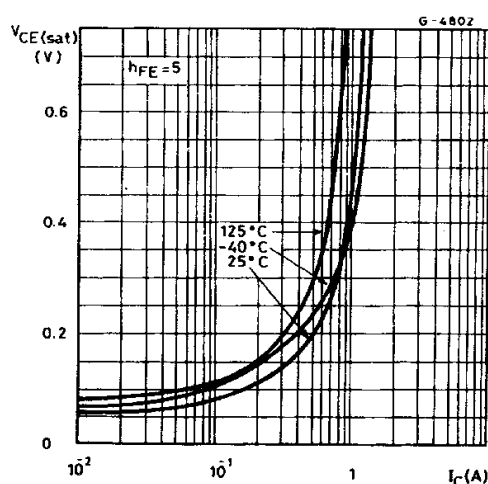
DC Current Gain



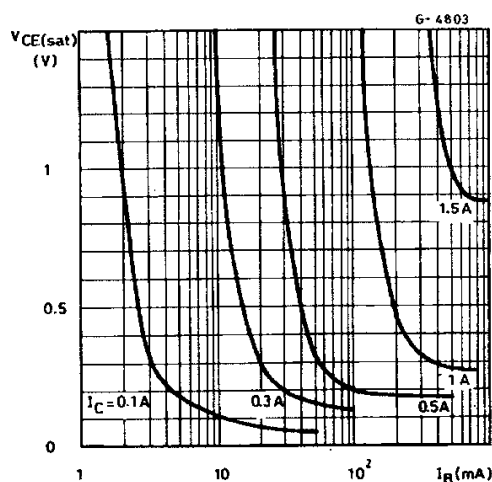
DC Current Gain



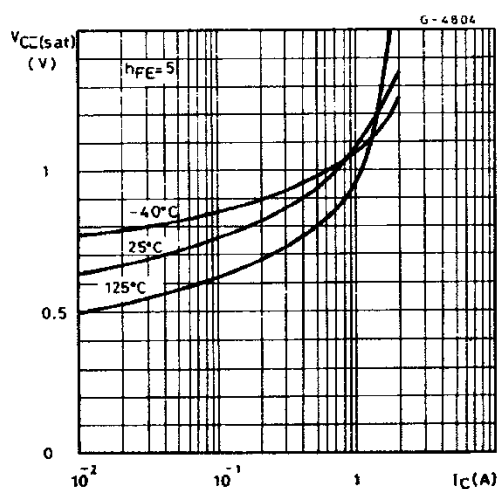
Collector-Emitter Saturation Voltage



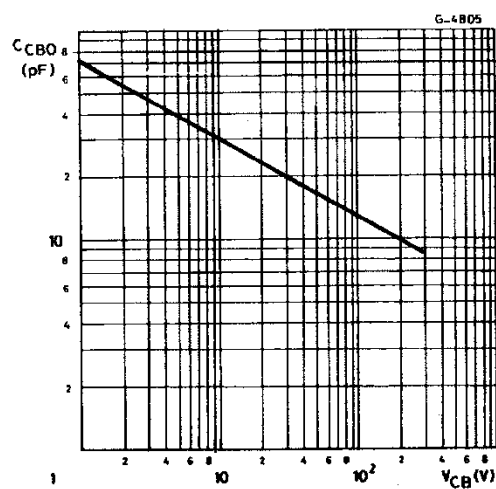
Collector-Emitter Saturation Voltage



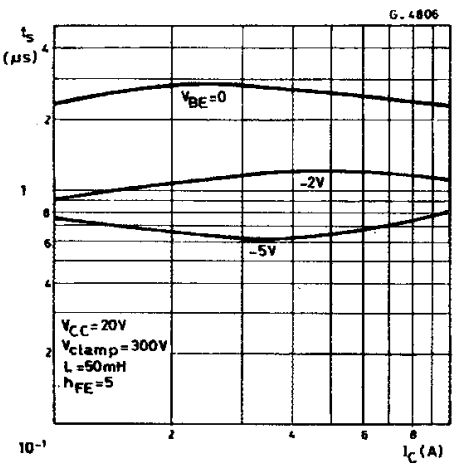
Base-Emitter Saturation Voltage



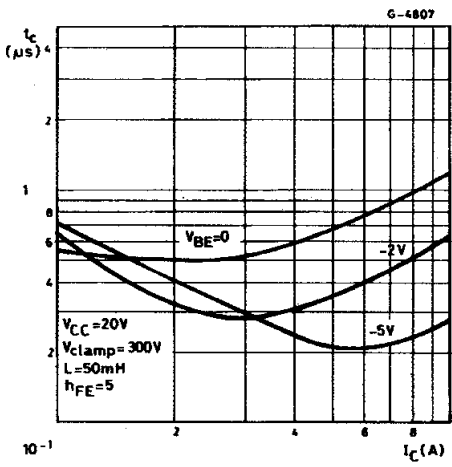
Collector-Base Capacitance



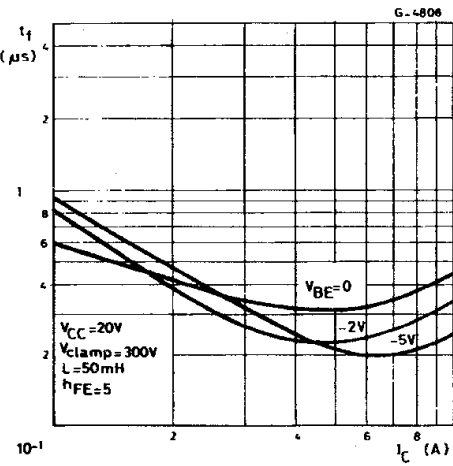
Switching Time Inductive Load



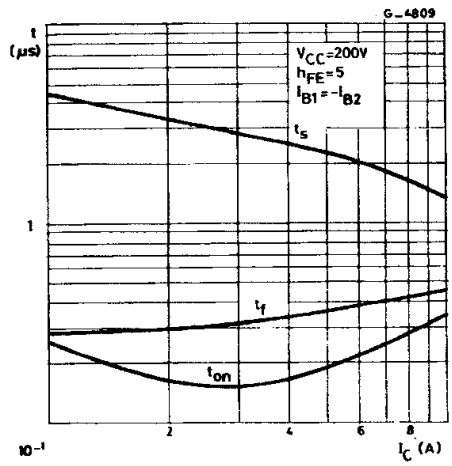
Switching Time Inductive Load



Switching Time Inductive Load

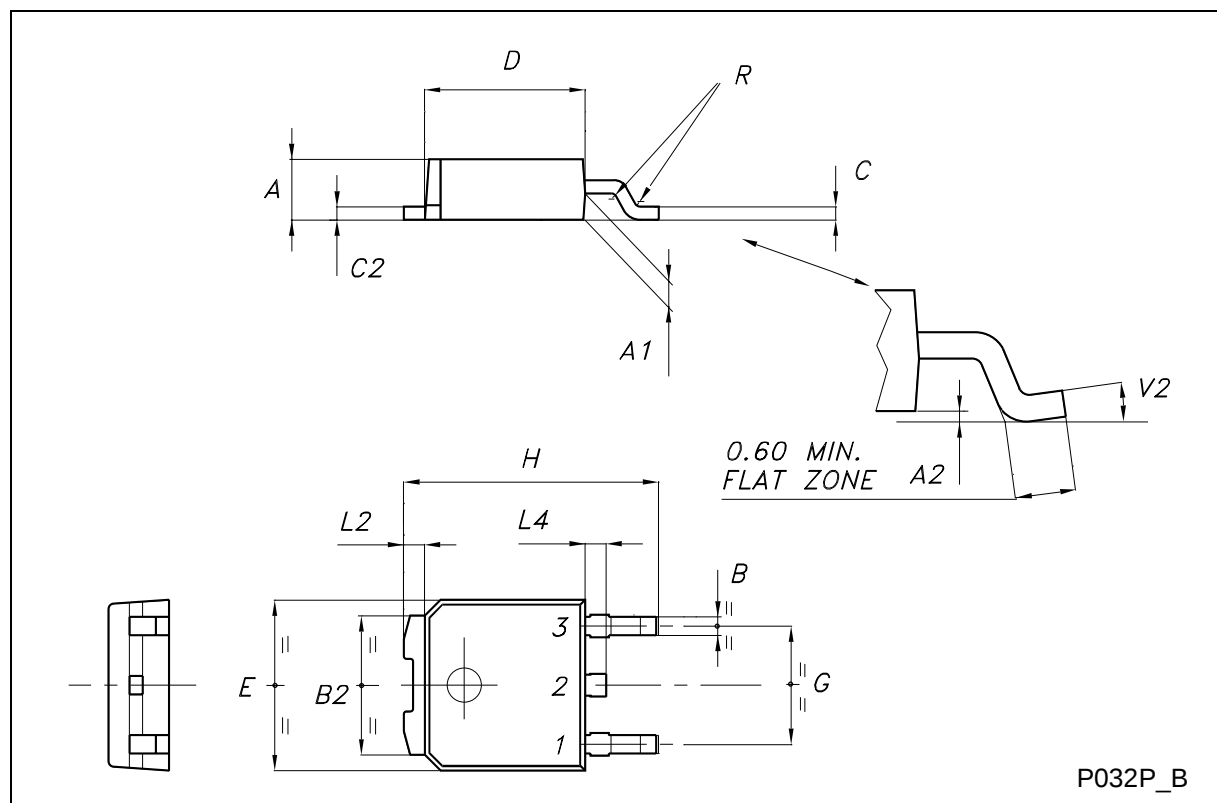


Switching Time Inductive Load



TO-252 (DPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
C	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
H	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0°



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